

1. General description

Planar passivated high commutation three quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series C" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in three quadrants only

3. Applications

- General purpose motor control circuits
- Home appliances
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

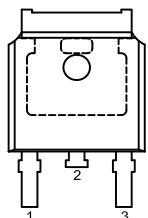
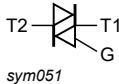
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|------|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 1000 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 107\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 4 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 25 | A |
| | | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | - | 27 | A |
| T_j | junction temperature | | - | - | 125 | °C |
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7 | 2 | 6 | 35 | mA |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|------|-----|------------------|
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7 | 2 | 8 | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7 | 2 | 20 | 35 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9 | - | - | 20 | mA |
| V_T | on-state voltage | $I_T = 5\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10 | - | 1.4 | 1.7 | V |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 670\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 1000 | 1500 | - | V/ μs |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 4\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | 3 | 30 | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|---|---|
| 1 | T1 | main terminal 1 |  <p>DPAK (SOT428)</p> |  <p>sym051</p> |
| 2 | T2 | main terminal 2[1] | | |
| 3 | G | gate | | |
| mb | T2 | mounting base; main terminal 2 | | |

[1] It is not possible to connect to pin 2 of the SOT428 package.

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|---------|---|---------|
| | Name | Description | Version |
| BTA204S-1000C | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|--|-----|------|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 1000 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 107\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 4 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | 25 | A |
| | | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | 27 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; SIN | - | 3.1 | A ² s |
| di_T/dt | rate of rise of on-state current | $I_G = 70\text{ mA}$ | - | 100 | A/ μ s |
| I_{GM} | peak gate current | | - | 2 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T_{stg} | storage temperature | | -40 | 150 | °C |
| T_j | junction temperature | | - | 125 | °C |

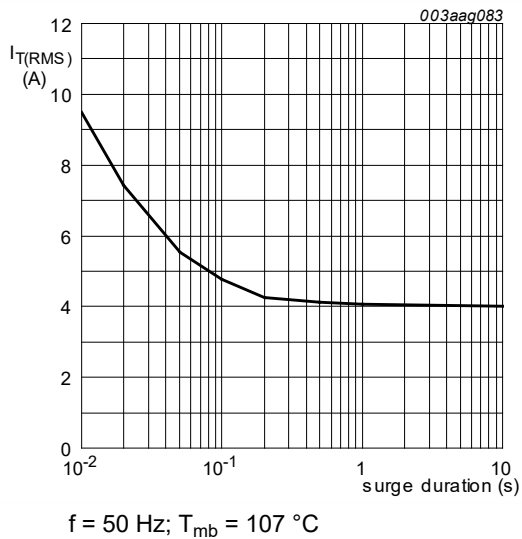


Fig. 1. RMS on-state current as a function of surge duration; maximum values

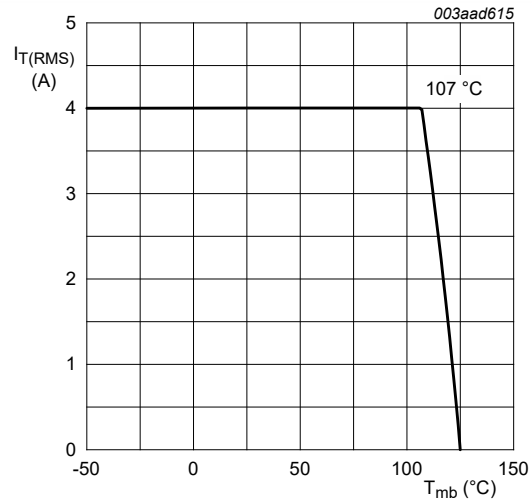


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

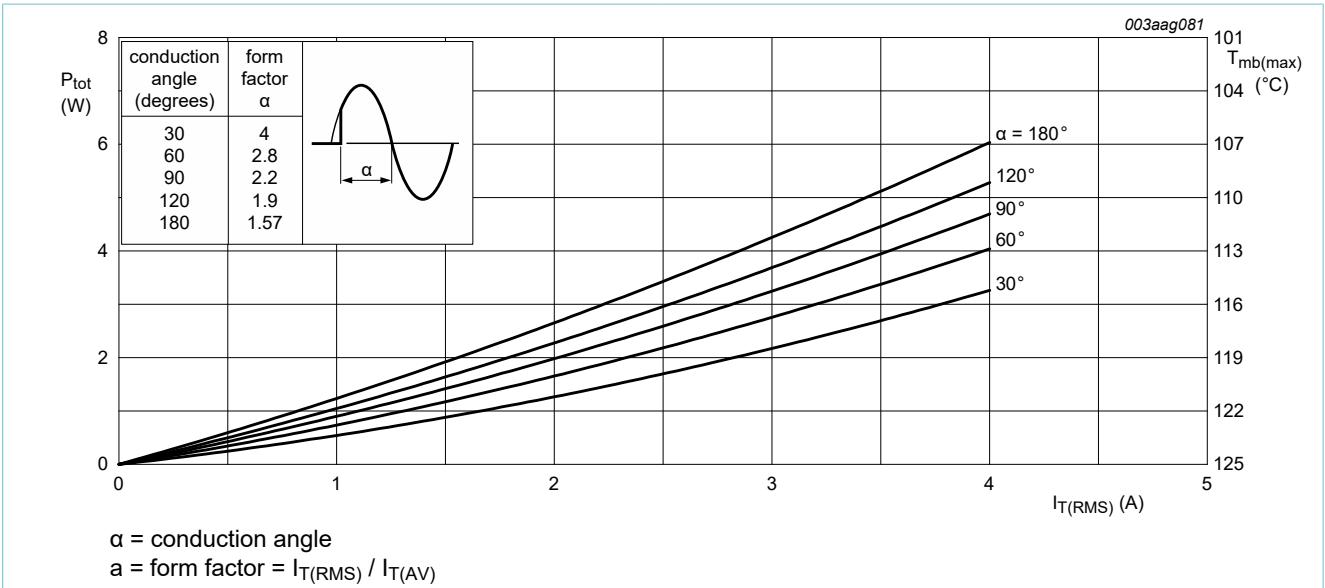


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

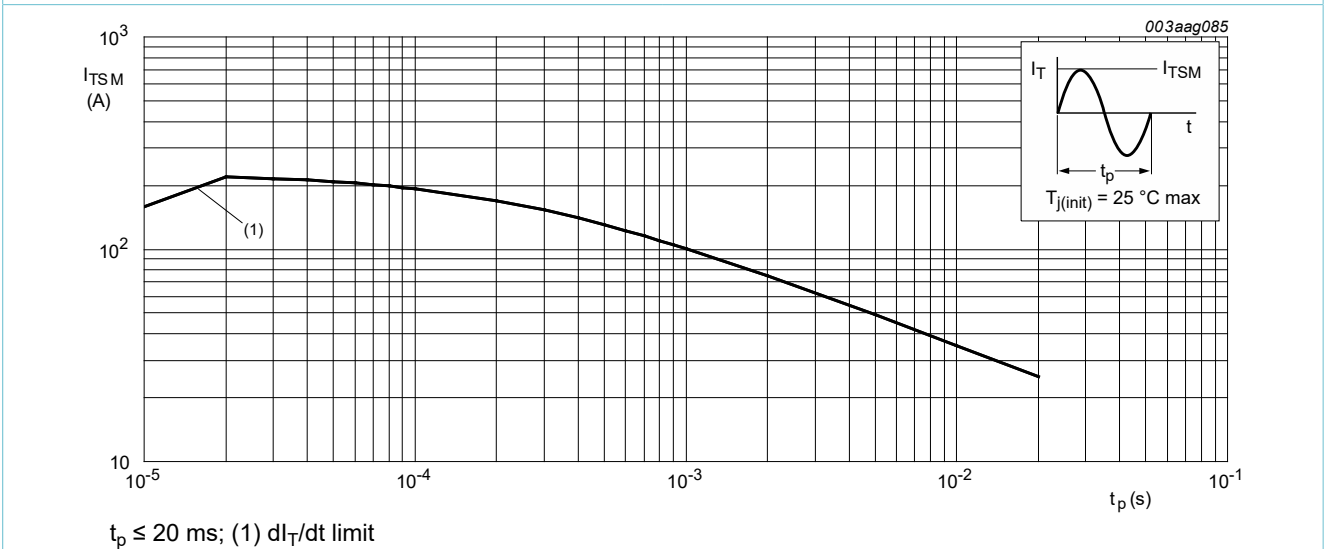
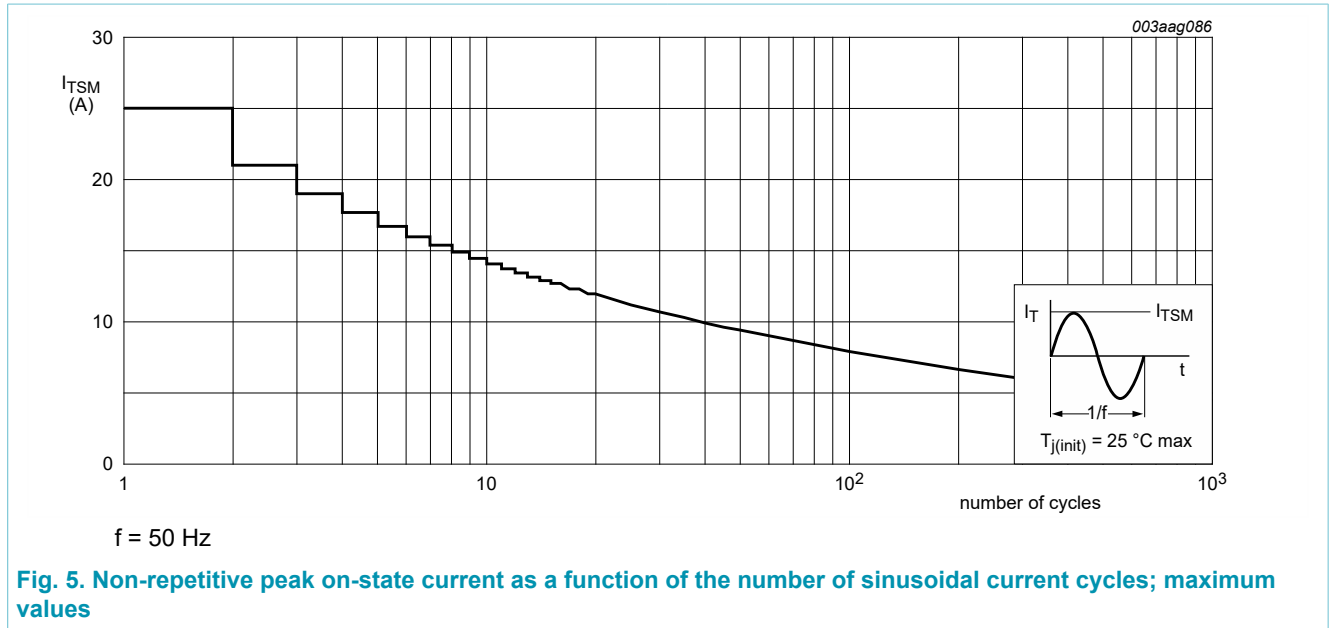


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

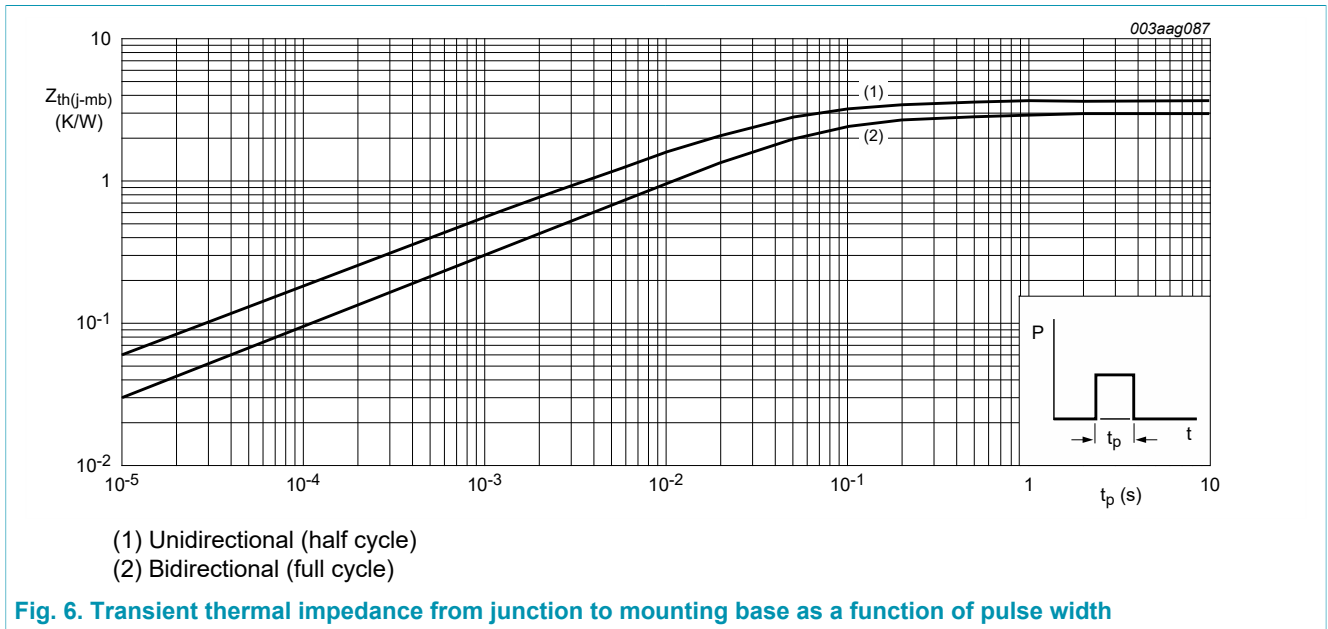


8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | - | - | 3 | K/W |
| | | half cycle; Fig. 6 | - | - | 3.7 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | [1] | - | 75 | - | K/W |

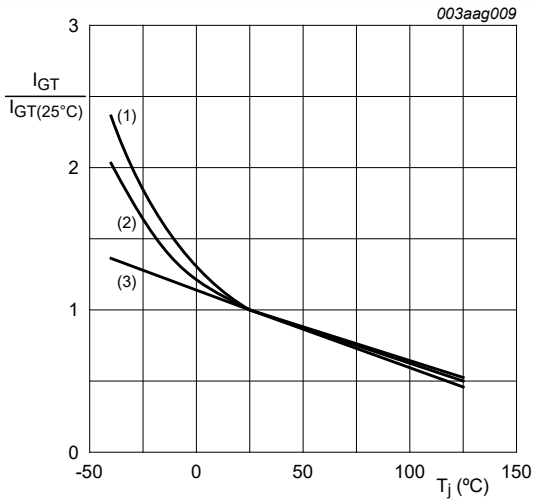
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|------|-----|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7 | 2 | 6 | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7 | 2 | 8 | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7 | 2 | 20 | 35 | mA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 20 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 30 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 20 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9 | - | - | 20 | mA |
| V_T | on-state voltage | $I_T = 5\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.4 | 1.7 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11 | - | 0.7 | 1 | V |
| | | $V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 11 | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = 1000\text{ V}$; $T_j = 125\text{ °C}$ | - | 0.1 | 0.5 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 670\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 1000 | 1500 | - | V/ μ s |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 4\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | 3 | 30 | - | A/ms |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

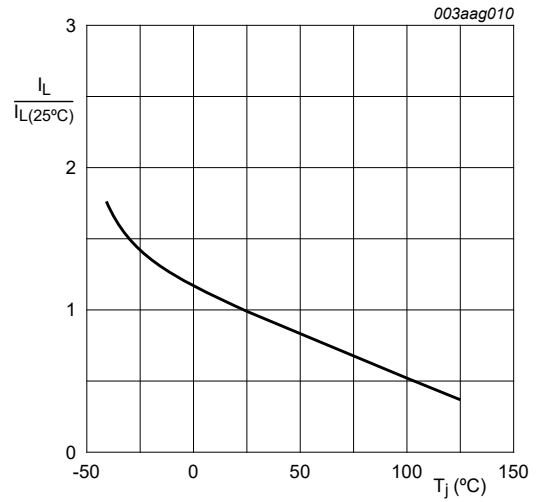


Fig. 8. Normalized latching current as a function of junction temperature

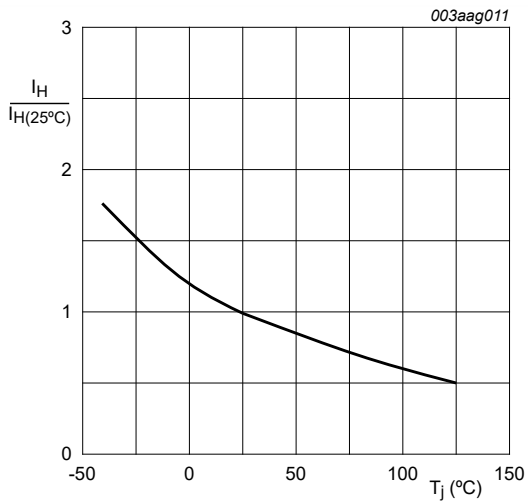
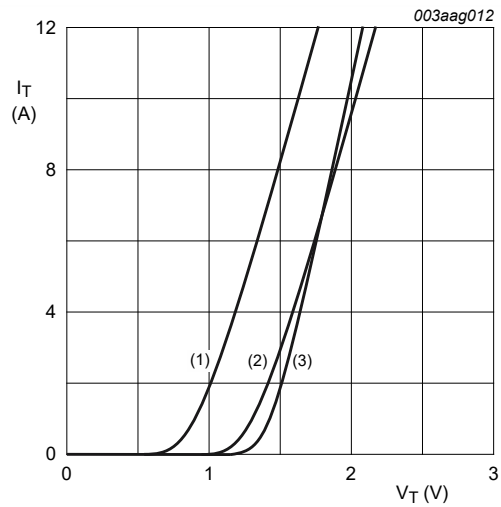


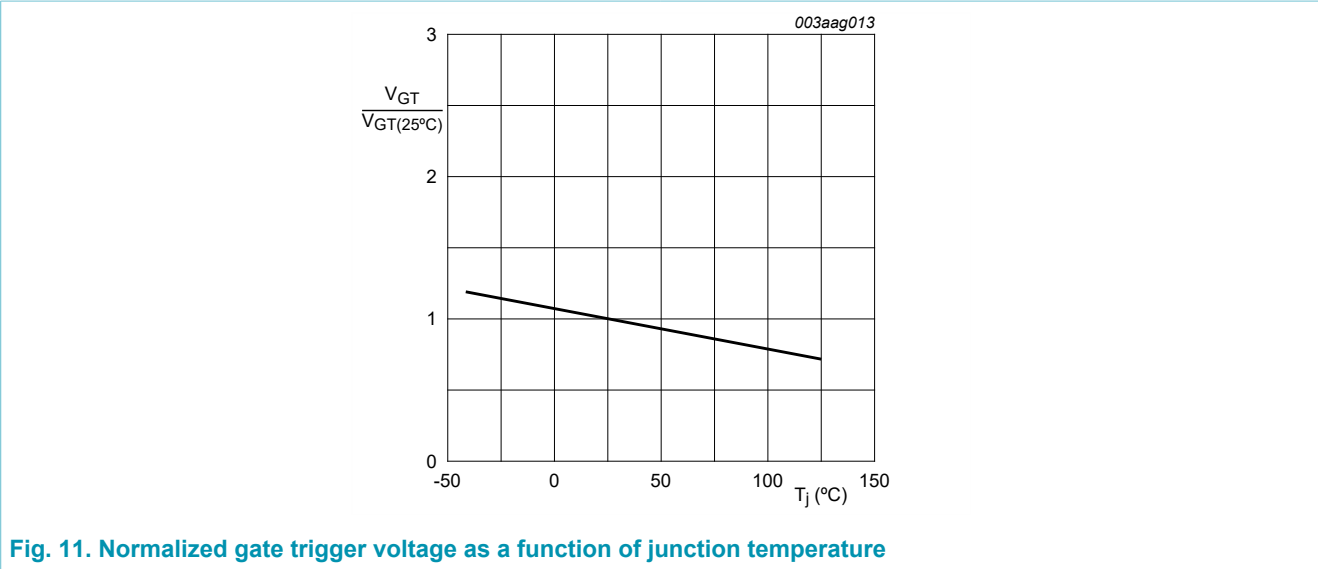
Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.22\text{ V}; R_s = 0.04\ \Omega$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage



10. Package outline



Fig. 12. Package outline DPAK (SOT428)

11. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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